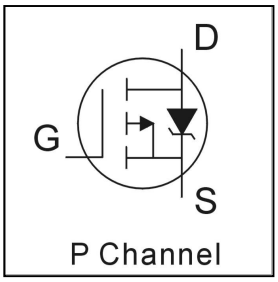
Gunter Semiconductor GmbH	GFC9120

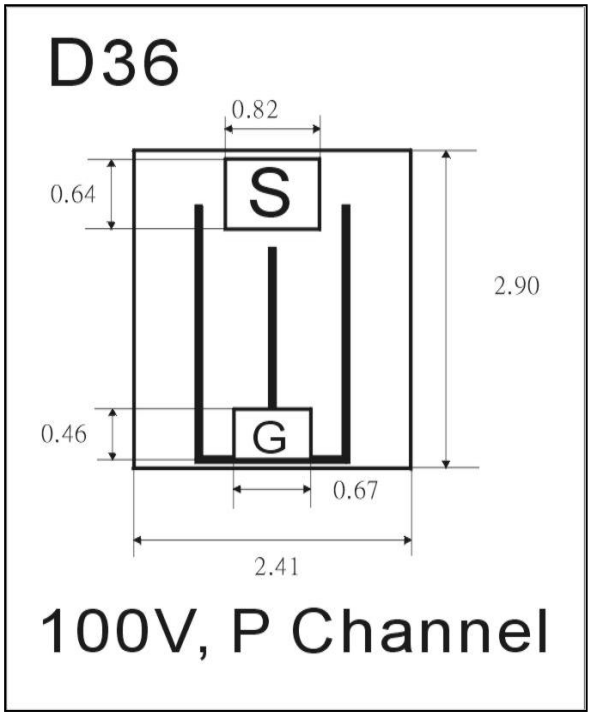
P Channel Power MOSFET

Chip Specification



General Description:

* Advanced Process Technology
* Dynamic dV/dt Rating
* **175℃ Operating Temperature**
* **Fast Switching**
* **Fully Avalanche Rated**



Mechanical Data:

D36	
Dimension	**2.41mm x 2.90mm**
Thickness:	**400 μm**
Metallization**:**	
Top : :	**Al**
Backside :	**CrNiAg / Au**
Suggested Bonding Conditions:	
Die Mounting:	**Solder Perform**
95/5 PbSn or 92.5./2.5/5 PbAgIn	
Source Bonding Wire**:**	**8 mil Al**

Absolute Maximum Rating **@Ta=25℃**

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	-V(BR)DSS	100	V	– VGS=0V, -ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.6	Ω	– VGS=10V, - ID=4.1A
Continuous Drain current (in target package)	--ID@25℃	6.8	A	- VGS=10V
Continuous Drain current (in target package)	--ID@100℃	4.8	A	- VGS=10V
Operation Junction Temperatre	Tj	-55~175	℃	
Storage Temperature	TSTR	-55~175	℃	

Target Device: IRF9520

TO-220AB	PD	60	W	@Tc=25℃